

B¹
cont.
supplying etching gas to the plasma etching reactor and energizing the etching gas into a plasma state, the etching gas including at least one fluorocarbon reactant and at least one oxygen reactant supplied to the plasma etching reactor at a flow rate ratio of oxygen reactant to fluorocarbon reactant of 1.5 or less;

C¹
uncl.
etching exposed portions of the silicon nitride layer with the plasma so as to etch openings in the silicon nitride layer with the plasma while providing an etch rate selectivity of the etching rate of the silicon nitride layer to the etching rate of the dielectric layer of at least about 5.

B²
21. (New) The process of claim 1, wherein the plasma reactor pressure is at a pressure above 80 mTorr.

22. (New) The process of claim 1, wherein the fluorocarbon reactant is supplied to the plasma reactor at a flow rate of 20 to 40 sccm and the oxygen reactant is supplied to the plasma reactor at a flow rate of 20 to 40 sccm.

23. (New) The process of claim 1, wherein the reactor comprises a capacitively coupled plasma reactor.
